

M22101 M22102

4 X 4 X 2 CROSSPOINT SWITCHES WITH CONTROL MEMORY

- LOW ON RESISTANCE 75Ω TYP AT $V_{DD} = 12 V$
- "BUILT-IN" LATCHED INPUTS
- LARGE ANALOG SIGNAL CAPACITY ± V_{DD}/2
- 10 MHz SWITCH BANDWITH
- MATCHED SWITCH CHARACTERISTICS
- $\Delta \text{ RON} = 8 \Omega \text{ TYP}, \text{ AT } V_{\text{DD}} = 12 \text{ V}$
- HIGH LINEARITY 0.25 % DISTORTION TYP, AT f = 1 kHz, V_{IN} = 5 V, V_{DD} V_{SS} = 10 V AND RI = 1 Ω
- STANDARD CMOS NOISE IMMUNITY

DESCRIPTION

The **M22101** and **M22102** crosspoint switches consist of 4 x 4 x 2 arrays of crosspoints (transmission gates), 4-line to 16-line decoders, and 16 latch circuits. Any one of the sixteen crosspoint pairs can be selected by applying the appropriate four-line address and any number of crosspoint pairs can be ON simultaneously. Corresponding crosspoints in each array are turned on and OFF simultaneously, also.

In the **M22101**, the selected crosspoint pair can be turned on or off by applying a logical ONE or ZERO, respectively, to the data input, and applying a ONE to the strobe input. When the device is "power-up", the state of the 16 switches is indeterminate.

PIN CONNECTIONS



Therefore all switches must be turned off by putting the strobe hight, data-in-low, and the addressing all switches in succession.

The selected pair of crosspoints in the **M22102** is turned on by applying a logical ONE to the K_a (set) input while a logical ZERO is on the K_b (reset) input, and turned off by applying a logical ONE to the K_b input while a logical ZERO is on the K_a input. In this respect the control latches of the **M22102** are similar to SET/RESET flip-flops. They differ, however, in that the simultaneous application of ONEs to the K_a and K_b inputs turns off (resets) all crosspoints. All crosspoints in both devices must be turned off as V_{DD} is applied.



ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage: Ceramic Type Plastic Type	-0.5 to +20 -0.5 to +18	V V
Vi	Input Voltage	-0.5 to V _{DD} + 0.5	V
l _l	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor	200	mW
	for Top = Full Package Temperature Range	100	mW
T _{op}	Operating Temperature: Ceramic Type Plastic Type	-55 to +125 -40 to +85	°C ℃
T _{stg}	Storage Temperature	-65 to +150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage: Ceramic Type	3 to 18	V
	Plastic Type	3 to 15	V
VI	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature: Ceramic Type	-55 to +125	°C
	Plastic Type	-40 to +85	°C

CONTROL TRUTH TABLE FOR M22101

Function		Add	ress		Strobe	Data	Select	
runction	Α	В	С	D	Strobe	Data		
Switch-on	1	1	1	1	1	1	(X4 Y4) & (X4' Y4')	
Switch-off	1	1	1	1	1	0	(X4 Y4) & (X4' Y4')	
No Change	Х	Х	X	X	0	Х	XXXX	

Note: 1 = High, 0 = Low, X = Don't Care

CONTROL TRUTH TABLE FOR M22102

Function		Add	ress		Strobe	Data	Select
Function	Α	В	С	D	Slibbe	Dala	Select
Switch-on	1	1	1	1	1	0	(X4 Y4) & (X4' Y4')
Switch-off	1	1	1	1	0	1	(X4 Y4) & (X4' Y4')
All Switch-off	Х	Х	X	X	1	1	All
No Change	Х	x	X	X	0	0	XXXX

Note: 1 = High, 0 = Low, X = Don't Care



Address		Sol	Select			ress		Select			
Α	В	С	D	Select		Α	В	С	D	5	eci
0	0	0	0	X1 Y1	X1' Y1'	0	0	0	1	X1 Y3	X1' Y3'
1	0	0	0	X2 Y1	X2' Y1'	1	0	0	1	X2 Y3	X2' Y3'
0	1	0	0	X3 Y1	X3' Y1'	0	1	0	1	X3 Y3	X3' Y3'
1	1	0	0	X4 Y1	X4' Y1'	1	1	0	1	X4 Y3	X4' Y3'
0	0	1	0	X1 Y2	X1' Y2'	0	0	1	1	X1 Y4	X1' Y4'
1	0	1	0	X2 Y2	X2' Y2'	1	0	1	1	X2 Y4	X2' Y4'
0	1	1	0	X3 Y2	X3' Y2'	0	1	1	1	X3 Y4	X3' Y4'
1	1	1	0	X4 Y2	X4' Y2'	1	1	1	1	X4 Y4	X4' Y4'

DECODER TRUTH TABLE

FUNCTIONAL AND BLOCK DIAGRAM



M22101/M22102

			Test Con	ditios	-	Value							
Symbol	Paramet	ter		Vi	VDD	TLC	w *		25 °C		Тни	GH *	Unit
				(V)	(V)	Min.	Max.	Min.	Тур.	Max.	Min.	Max.	
CROSS	POINT									-	-		
١L	Quiescent			5				0.04	5		150		
	Supply	F1			10				0.04	10		300	
	Current				15				0.04	20		600	μA
					20				0.08	100		3000	μA
					5				0.04	20		150	
		B1			10				0.04	40		300	
					15				0.04	80		600	
R _{ON}	On				5		450		225	1250		1625	
	Resistance	F1	Any Switch		10		135		85	180		230	
			,		12		100		75	135		175	
					15		70		65	95		125	Ω
					5		1000		225	1250		1440	
		B1	$V_{IS} = 0$ to V_{DD}		10		145		85	180		205	
					12		110		75	135		155	1
					15		75		65	95		110	
ΔON	Resistance A	R _{ON}			5				35				
	(Between an	y two			10				20				Ω
	channels)				12				18				
					15				15				
OFF Channel		F1	All Switch OFF	0/18	18		±0.1		±10 ⁻³	±0.1•		±1	μA
Leakage Current		B1		0/15	15		±0.3		±10 ⁻³	±0.3		±1	μΛ
CONTR	OL												
VIL	Input Low		OFF Switch		5		1.5			1.5		1.5	
	Voltage		I _L < 0.2 μA		10		3			3		3	V
					15		4			4		4	
VIH	Input High		ON Switch		5	3.5		3.5			3.5		
	Voltage		see R _{ON}		10	7		7			7		V
			Characteristics		15	11		11			11		
lı –	Input	F1	Any Control	0/18	18		±0.1		±10 ⁻⁵	±0.1		±1	μA
	Current	B1	Input	0/15	15		±0.3		±10 ⁻⁵	±0.3		±1	μη
Cı	Input Capaci	tance	Any Input						5	7.5			pF

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Determined by minimum feasible leakage measurement for automatic testing

* $T_{LOW} = -55$ °C for HCC device: -40 °C for HCF device.

* $T_{HIGH} = +125 \text{ °C}$ for **HCC** device: +85 °C for **HCF** device.

The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V



DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25 \ ^{\circ}C$, $C_{L} = 50 \ pF$, $R_{L} = 200 \ K\Omega$, typical temperature coefficent for all V_{DD} values is 03 %/ $^{\circ}C$, all input rise and fall times= 20 ns)

Symbol	Parameter	Test Condit	Test Conditions			Value			
Symbol	Falameter		$V_{DD}(V)$	Min.	Тур.	Max.	Unit		
t _{PHL} t _{PLH}	Propagation Delay Time Address or Strobe Inputs to Output	R _L = 10 KΩ			200		ns		
t _{PHL} t _{PLH}	Propagation Delay Time Across Crosspoint	$C_L = 50 \text{ pF}$	12		20		ns		
	Minimum Strobe Pulse Width				80		ns		



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Plastic DIP24 (0.25) MECHANICAL DATA

DIM.		mm				
2	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1		0.63			0.025	
b		0.45			0.018	
b1	0.23		0.31	0.009		0.012
b2		1.27			0.050	
D			32.2			1.268
E	15.2		16.68	0.598		0.657
е		2.54			0.100	
e3		27.94			1.100	
F			14.1			0.555
I		4.445			0.175	
L		3.3			0.130	





DIM.		mm		inch					
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.			
А			32.3			1.272			
В	13.05		13.36	0.514		0.526			
С	3.9		5.08	0.154		0.200			
D	3			0.118					
E	0.5		1.78	0.020		0.070			
e3		27.94			1.100				
F	2.29		2.79	0.090		0.110			
G	0.4		0.55	0.016		0.022			
I	1.17		1.52	0.046		0.060			
L	0.22		0.31	0.009		0.012			
М	1.52		2.49	0.060		0.098			
N1	4° (min.), 15° (max.)							
Р	15.4		15.8	0.606		0.622			
Q			5.71			0.225			

Ceramic DIP24 MECHANICAL DATA





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